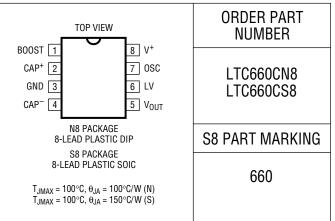
## **ABSOLUTE MAXIMUM RATINGS**

(Note 1)

Supply Voltage (V <sup>+</sup> )
Input Voltage on Pins 1, 6, 7 (Note 2)0.3V < V <sub>IN</sub> < (V <sup>+</sup> + 0.3V)
Output Short-Circuit Duration to GND
(Note 5) 1 sec
Power Dissipation 500mW
Operating Temperature Range 0°C to 70°C
Storage Temperature Range –65°C to 150°C
Lead Temperature (Soldering, 10 sec)

## PACKAGE/ORDER INFORMATION



Consult Factory for Industrial and Military grade parts.

## **ELECTRICAL CHARACTERISTICS**

V<sup>+</sup> = 5V, C1 and C2 = 150 $\mu$ F, Boost = Open, C<sub>OSC</sub> = OpF, T<sub>A</sub> = 25°C, unless otherwise noted.

SYMBOL	PARAMETER CONDITIONS			ТҮР	MAX	UNITS
	Supply Voltage	R <sub>L</sub> = 1k Inverter, LV = Open Inverter, LV = GND Doubler, LV = V <sub>OUT</sub>	3 1.5 2.5		5.5 5.5 5.5	V V V
I <sub>S</sub>	Supply Current	No Load Boost = Open Boost = V <sup>+</sup>		0.08 0.23	0.5 3	mA mA
I <sub>OUT</sub>	Output Current	V <sub>OUT</sub> More Negative Than –4V				mA
R <sub>OUT</sub>	Output Resistance	I <sub>L</sub> = 100mA (Note 3)		6.5	10	Ω
f <sub>osc</sub>	Oscillator Frequency	Boost = Open Boost = V <sup>+</sup> (Note 4)		10 80		kHz kHz
	Power Efficiency	$ \begin{array}{c} R_L = 1k \mbox{ Connected Between V}^+ \mbox{ and } V_{OUT} \\ R_L = 500\Omega \mbox{ Connected Between V}_{OUT} \mbox{ and } GND \\ I_L = 100mA \mbox{ to } GND \end{array} $		98 96 88		% % %
	Voltage Conversion Efficiency	No Load		99.96		%
	Oscillator Sink or Source Current	Boost = Open Boost = V <sup>+</sup>		±1.1 ±5.0		μΑ μΑ

The  $\bullet$  denotes specifications which apply over the full operating temperature range; all other limits and typicals are at T<sub>A</sub> = 25°C.

**Note 1:** Absolute Maximum Ratings are those values beyond which the life of a device may be impaired.

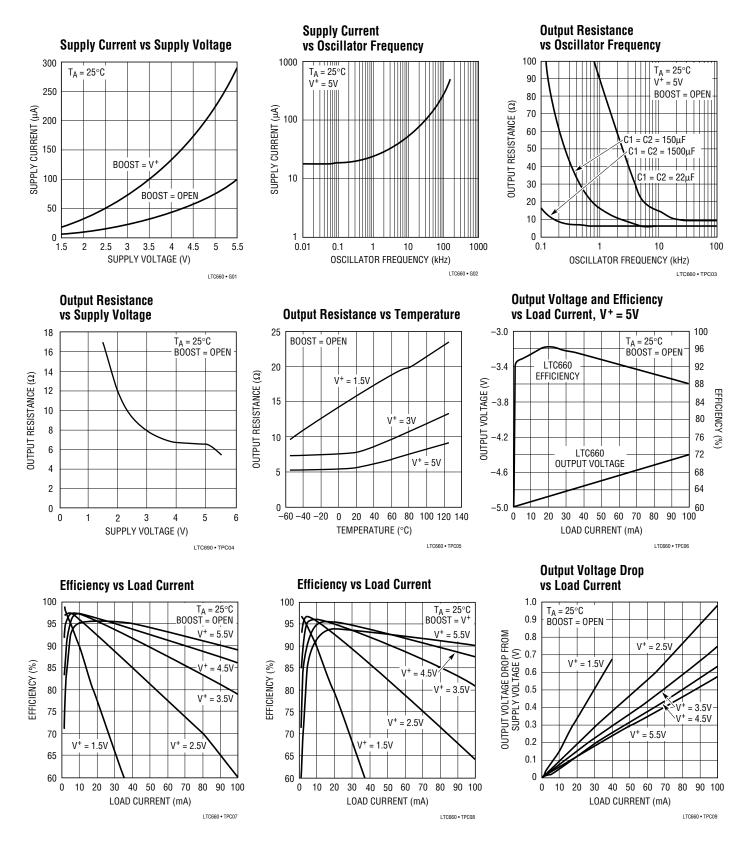
**Note 2:** Connecting any input terminal to voltages greater than V<sup>+</sup> or less than ground may cause destructive latch-up. It is recommended that no inputs from source operating from external supplies be applied prior to power-up of the LTC660.

**Note 3:** The output resistance is a combination of internal switch resistance and external capacitor ESR. To maximize output voltage and efficiency, keep external capacitor ESR <  $0.2\Omega$ .

**Note 4:**  $f_{OSC}$  is tested with  $C_{OSC} = 100pF$  to minimize the effects of test fixture capacitance loading. The 0pF frequency is correlated to this 100pF test point, and is intended to simulate the capacitance at Pin 7 when the device is plugged into a test socket and no external capacitor is used. **Note 5:** OUT may be shorted to GND for 1 sec without damage, but shorting OUT to V<sup>+</sup> may damage the device and should be avoided. Also, for temperatures above 85°C, OUT must not be shorted to GND or V<sup>+</sup>, even instantaneously, or device damage may result.

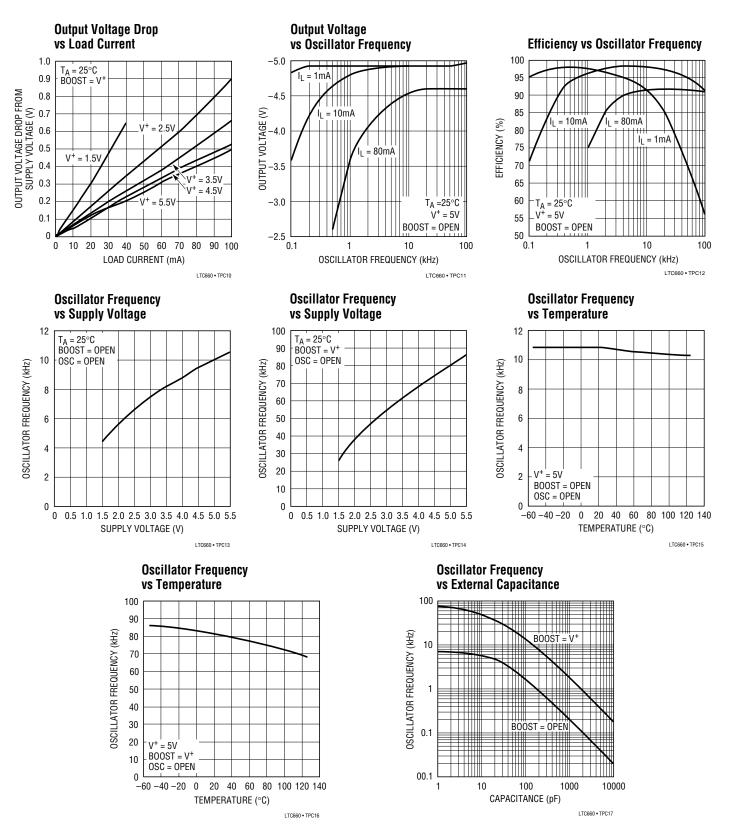


### TYPICAL PERFORMANCE CHARACTERISTICS (Using Test Circuit in Figure 1)





## TYPICAL PERFORMANCE CHARACTERISTICS (Using Test Circuit in Figure 1)





# PIN FUNCTIONS

PIN	NAME	INVERTER	DOUBLER	
1	BOOST	Internal Oscillator Frequency Control Pin. BOOST = Open, f <sub>OSC</sub> = 10kHz typ; BOOST = V <sup>+</sup> , f <sub>OSC</sub> = 80kHz typ; when OSC is driven externally BOOST has no effect.	Same	
2	CAP+	Positive Terminal for Charge Pump Capacitor	Same	
3	GND	Power Supply Ground Input	Positive Voltage Input	
4	CAP-	Negative Terminal for Charge Pump Capacitor	Same	
5	V <sub>OUT</sub>	Negative Voltage Output	Power Supply Ground Input	
6	LV	Tie LV to GND when the input voltage is less than 3V. LV may be connected to GND or left open for input voltages above 3V. Connect LV to GND when overdriving OSC.	LV must be tied to $V_{\mbox{OUT}}$ for all input voltages.	
7	OSC	An external capacitor can be connected to this pin to slow the oscillator frequency. Keep stray capacitance to a minimum. An external oscillator can be applied to this pin to overdrive the internal oscillator.	Same except standard logic levels will not be able to overdrive OSC pin.	
8	V+	Positive Voltage Input	Positive Voltage Output	

# **TEST CIRCUIT**

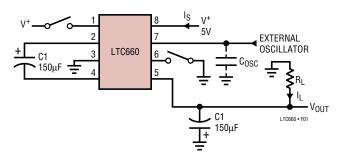


Figure 1. Test Circuit



## **APPLICATIONS INFORMATION**

### Theory of Operation

To understand the theory of operation for the LTC660, a review of a basic switched-capacitor building block is helpful. In Figure 2, when the switch is in the left position, capacitor C1 will charge to voltage V1. The total charge on C1 will be q1 = C1V1. The switch then moves to the right, discharging C1 to voltage V2. After this discharging time, the charge on C1 is q2 = C1V2. Note that charge has been transferred from the source V1 to the output V2. The amount of charge transferred is:

 $\Delta q = q1 - q2 = C1 (V1 - V2)$ 

If the switch is cycled "f" times per second, the charge transfer per unit time (i.e., current) is:

 $I = f \bullet \Delta q = f \bullet C1 (V1 - V2)$ 

Rewriting in terms of voltage and impedance equivalence,

$$I = \frac{V1 - V2}{1/fC1} = \frac{V1 - V2}{R_{FQUIV}}$$

A new variable  $R_{EQUIV}$  has been defined such that  $R_{EQUIV} = 1/fC1$ . Thus, the equivalent circuit for the switched-capacitor network is as shown in Figure 3.

Figure 4 shows that the LTC660 has the same switching action as the basic switched-capacitor building block.

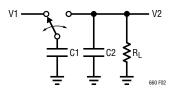
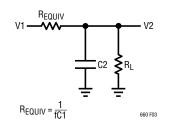


Figure 2. Switched-Capacitor Building Block





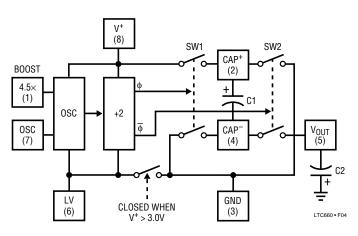


Figure 4. LTC660 Switched-Capacitor Voltage Converter Block Diagram

This simplified circuit does not include finite on-resistance of the switches and output voltage ripple, however, it does give an intuitive feel for how the device works. For example, if you examine power conversion efficiency as a function of frequency this simple theory will explain how the LTC660 behaves. The loss and hence the efficiency is set by the output impedance. As frequency is decreased, the output impedance will eventually be dominated by the 1/fC1 term and voltage losses will rise decreasing the efficiency. As the frequency increases the quiescent current increases. At high frequency this current loss becomes significant and the power efficiency starts to decrease.

The LTC660 oscillator frequency is designed to run where the voltage loss is a minimum. With the external  $150\mu$ F capacitors the effective output impedance is determined by the internal switch resistances and the capacitor ESRs.

### LV (Pin 6)

The internal logic of the LTC660 runs between V<sup>+</sup> and LV (Pin 6). For V<sup>+</sup> $\geq$  3V, an internal switch shorts LV to ground (Pin 3). For V<sup>+</sup> < 3V, the LV pin should be tied to ground. For V<sup>+</sup> $\geq$  3V, the LV pin can be tied to ground or left floating.

### OSC (Pin 7) and BOOST (Pin 1)

The switching frequency can be raised, lowered or driven from an external source. Figure 5 shows a functional diagram of the oscillator circuit.



### **APPLICATIONS INFORMATION**

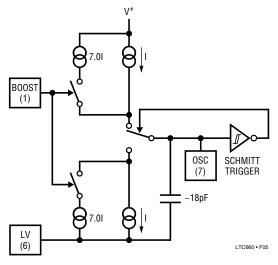
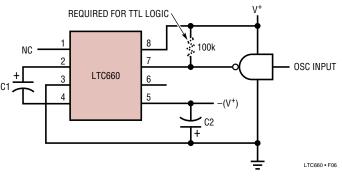


Figure 5. Oscillator

By connecting the BOOST pin (Pin 1) to V<sup>+</sup>, the charge and discharge current is increased and, hence, the frequency is increased by approximately four and a half times. Increasing the frequency will decrease output impedance and ripple for high load currents.

Loading Pin 7 with more capacitance will lower the frequency. Using the BOOST (Pin 1) in conjunction with external capacitance on Pin 7 allows user selection of the frequency over a wide range.

Driving the LTC660 from an external frequency source can be easily achieved by driving Pin 7 and leaving the BOOST pin open, as shown in Figure 6. The output current from Pin 7 is small, typically  $1.1\mu$ A to  $8\mu$ A, so a logic gate is capable of driving this current. (A CMOS logic gate can be used to drive the OSC pin.) For 5V applications, a TTL logic gate can be used by simply adding an external pull-up resistor (see Figure 6).



**Figure 6. External Clocking** 

#### **Capacitor Selection**

While the exact values of C1 and C2 are noncritical, good quality, low ESR capacitors are necessary to minimize voltage losses at high currents. For C1 the effect of the ESR of the capacitor will be multiplied by four, due to the fact the switch currents are approximately two times higher than the output current and losses will occur on both the charge and discharge cycle. This means using a capacitor with  $1\Omega$  of ESR for C1 will have the same effect as increasing the output impedance of the LTC660 by  $4\Omega$ . This represents a significant increase in the voltage losses. For C2 the effect of ESR is less dramatic. A C2 with  $1\Omega$  of ESR will increase the output impedance by  $1\Omega$ . The size of C2 and the load current will determine the output voltage ripple. It is alternately charged and discharged at a current approximately equal to the output current. This will cause a step function to occur in the output voltage at the switch transitions. For example, for a switching frequency of 5kHz (one-half the nominal 10kHz oscillator frequency) and C2 =  $150\mu$ F with an ESR of 0.2 $\Omega$ , ripple is approximately 90mV with a 100mA load current.



## TYPICAL APPLICATIONS

#### Negative Voltage Converter

Figure 7 shows a typical connection which will provide a negative supply from an available positive supply. This circuit operates over full temperature and power supply ranges without the need of any external diodes. The LV pin (Pin 6) is shown grounded, but for V<sup>+</sup>  $\ge$  3V, it may be floated, since LV is internally switched to ground (Pin 3) for V<sup>+</sup>  $\ge$  3V.

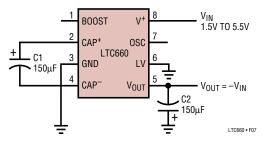


Figure 7. Voltage Inverter

The output voltage (Pin 5) characteristics of the circuit are those of a nearly ideal voltage source in series with a  $6.5\Omega$ resistor. The  $6.5\Omega$  output impedance is composed of two terms: 1) the equivalent switched-capacitor resistance (see Theory of Operation), and 2) a term related to the onresistance of the MOS switches.

At an oscillator frequency of 10kHz and C1 =  $150\mu$ F, the first term is:

$$R_{EQUIV} = \frac{1}{(f_{OSC}/2)C1} = \frac{1}{5 \cdot 10^3 \cdot 150 \cdot 10^{-6}} = 1.3\Omega.$$

Notice that the equation for  $R_{EQUIV}$  is not a capacitive reactance equation ( $X_C = 1/\omega C$ ) and does not contain a  $2\pi$  term.

The exact expression for output impedance is complex, but the dominant effect of the capacitor is clearly shown on the typical curves of output impedance and power efficiency versus frequency. For C1 = C2 =  $150\mu$ F, the output impedance goes from  $6.5\Omega$  at  $f_{OSC} = 10$ kHz to  $110\Omega$  at  $f_{OSC} = 100$ Hz. As the 1/fC term becomes large compared to the switch on-resistance term, the output resistance is determined by 1/fC only.

### Voltage Doubling

Figure 8 shows the LTC660 operating in the voltage doubling mode. The external Schottky (1N5817) diode is for start-up only. The output voltage is  $2 \cdot V_{IN}$  without a load. The diode has no effect on the output voltage.

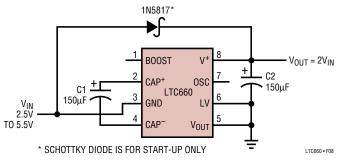


Figure 8. Voltage Doubler

### Ultraprecision Voltage Divider

An ultraprecision voltage divider is shown in Figure 9. To achieve the 0.002% accuracy indicated, the load current should be kept below 100nA. However, with a slight loss in accuracy, the load current can be increased.

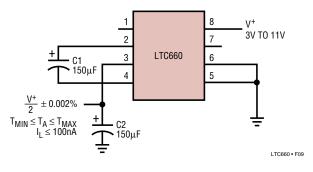


Figure 9. Ultraprecision Voltage Divider

### **Battery Splitter**

A common need in many systems is to obtain positive and negative supplies from a single battery or single power supply system. Where current requirements are small, the circuit shown in Figure 10 is a simple solution. It provides symmetrical positive or negative output voltages, both equal to one-half the input voltage. The output voltages are both referenced to Pin 3 (Output Common).



### TYPICAL APPLICATIONS

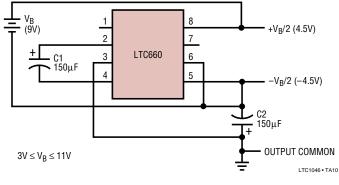


Figure 10. Battery Splitter

#### Paralleling for Lower Output Resistance

Additional flexibility of the LTC660 is shown in Figures 11 and 12. Figure 11 shows two LTC660s connected in parallel to provide a lower effective output resistance. If, however, the output resistance is dominated by 1/fC1, increasing the capacitor size (C1) or increasing the frequency will be of more benefit than the paralleling circuit shown.

#### **Stacking for Higher Voltage**

Figure 12 makes use of "stacking" two LTC660s to provide even higher voltages. In Figure 12, a negative voltage doubler or tripler can be achieved depending upon how Pin 8 of the second LTC660 is connected, as shown schematically by the switch.

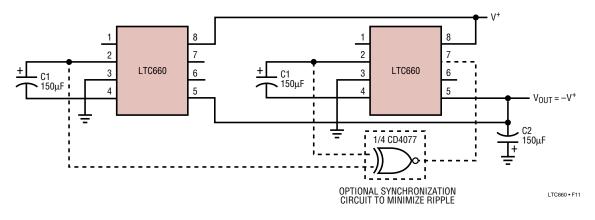
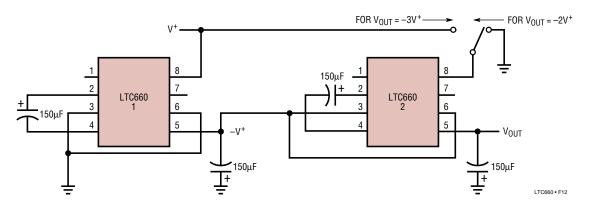
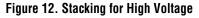


Figure 11. Paralleling for 200mA Load Current

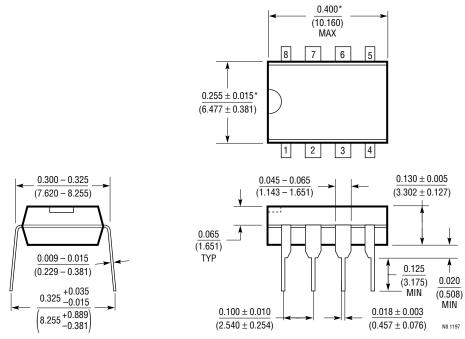






### **PACKAGE DESCRIPTION** Dimensions in inches (millimeters) unless otherwise noted.

N8 Package 8-Lead PDIP (Narrow 0.300) (LTC DWG # 05-08-1510)



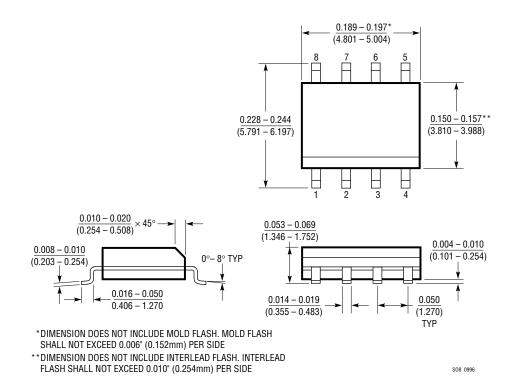
\*THESE DIMENSIONS DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.010 INCH (0.254mm)





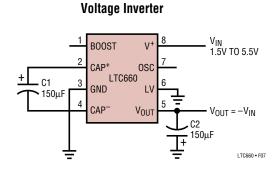
# **PACKAGE DESCRIPTION** Dimensions in inches (millimeters) unless otherwise noted.

S8 Package 8-Lead Plastic Small Outline (Narrow 0.150) (LTC DWG # 05-08-1610)

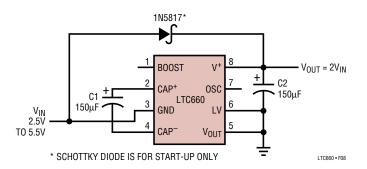




# TYPICAL APPLICATIONS



#### Voltage Doubler



### **RELATED PARTS**

PART NUMBER	OUTPUT CURRENT	MAXIMUM V <sub>IN</sub>	COMMENTS	
Unregulated Output Voltag	e			
LTC660	100mA	6V	Highest Current	
LTC1046	50mA	6V		
LTC1044	20mA	9.5V	Lowest Cost	
LTC1044A	20mA	13V		
LTC1144	20mA	20V	Highest Voltage	
Regulated Output Voltage	·		-	
LT1054	100mA	16V	Adjustable Output	
LTC1262	30mA	6V	12V Fixed Output	
LTC1261	10mA	9V	-4V, -4.5V and Adjustable Outputs	

All devices are available in plastic 8-lead SO and PDIP packages